

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (π-MOSV)

2SJ610

Switching Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance: $R_{DS(ON)} = 1.85 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 18 S$ (typ.)
- Low leakage current: $I_{DSS} = -100 \mu A$ ($V_{DS} = -250 V$)
- Enhancement-mode: $V_{th} = -1.5 \sim -3.5 V$ ($V_{DS} = 10 V$, $I_D = 1 mA$)

Maximum Ratings ($T_c = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-250	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	-250	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	-2.0	A
	Pulse ($t = 1 ms$) (Note 1)	I_{DP}	-4.0	
Drain power dissipation		P_D	20	W
Single pulse avalanche energy (Note 2)		E_{AS}	180	mJ
Avalanche current		I_{AR}	-2.0	A
Repetitive avalanche energy (Note 3)		E_{AR}	2.0	mJ
Channel temperature		T_{ch}	150	$^\circ C$
Storage temperature range		T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

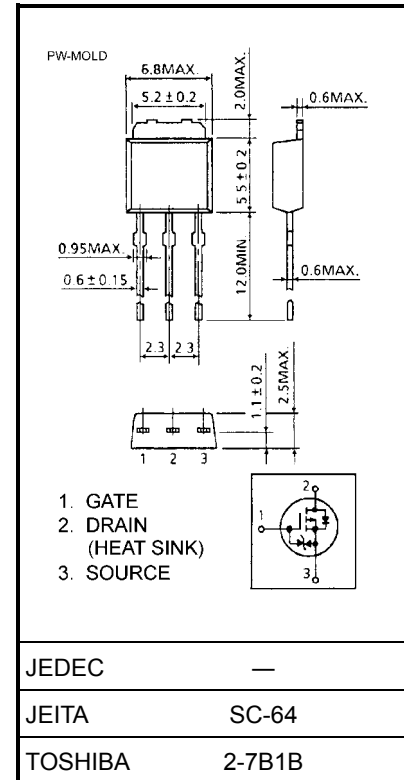
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^\circ C/W$

Note 1: Please use devices on condition that the channel temperature is below $150^\circ C$.

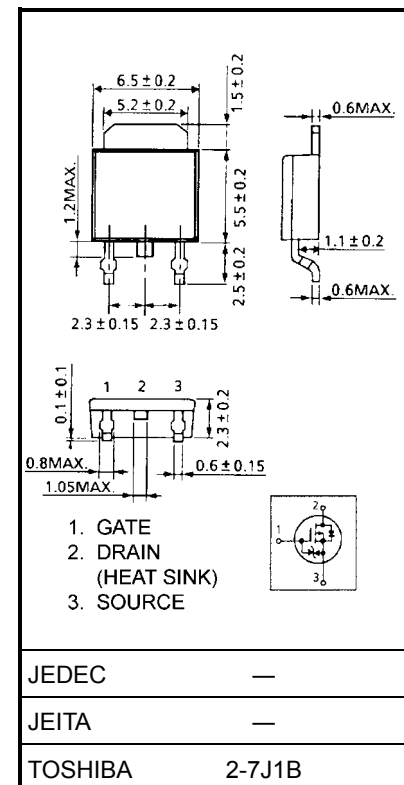
Note 2: $V_{DD} = -50 V$, $T_{ch} = 25^\circ C$ (initial), $L = 75 mH$, $I_{AR} = -2.0 A$, $R_G = 25 \Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

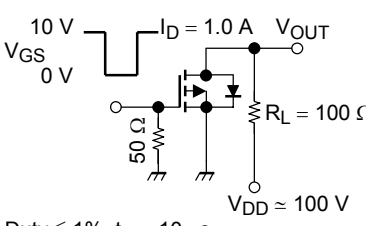


Weight: 0.36 g (typ.)



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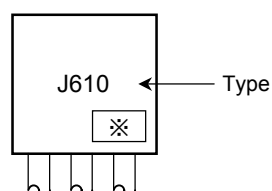
Electrical Characteristics (Tc = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = -250 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-250	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-1.5	—	-3.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -10 \text{ V}, I_D = -1.0 \text{ A}$	—	1.85	2.55	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -1.0 \text{ A}$	0.5	1.8	—	S
Input capacitance		C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	381	—	pF
Reverse transfer capacitance		C_{rss}		—	52	—	
Output capacitance		C_{oss}		—	157	—	
Switching time	Rise time	t_r		—	5	—	ns
	Turn-on time	t_{on}		—	20	—	
	Fall time	t_f		—	6	—	
	Turn-off time	t_{off}		—	36	—	
Total gate charge		Q_g	$V_{DD} \approx -200 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -2.0 \text{ A}$	—	24	—	nC
Gate-source charge		Q_{gs}		—	11	—	
Gate-drain charge		Q_{gd}		—	13	—	

Source-Drain Ratings and Characteristics (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	-2.0	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	-4.0	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = -2.0 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	2.0	V
Reverse recovery time	t_{rr}	$I_{DR} = -2.0 \text{ A}, V_{GS} = 0 \text{ V},$	—	120	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	540	—	nC

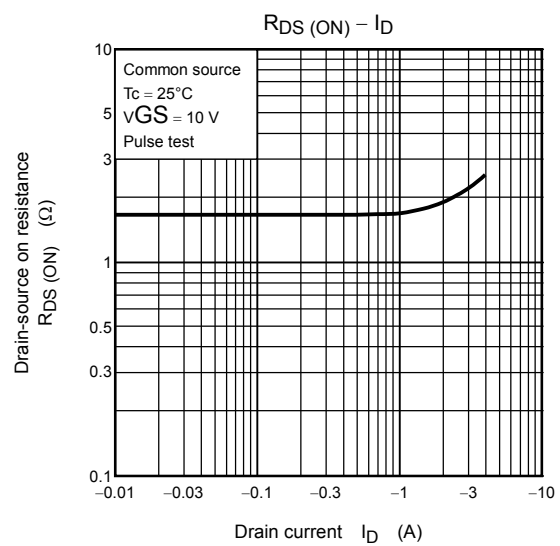
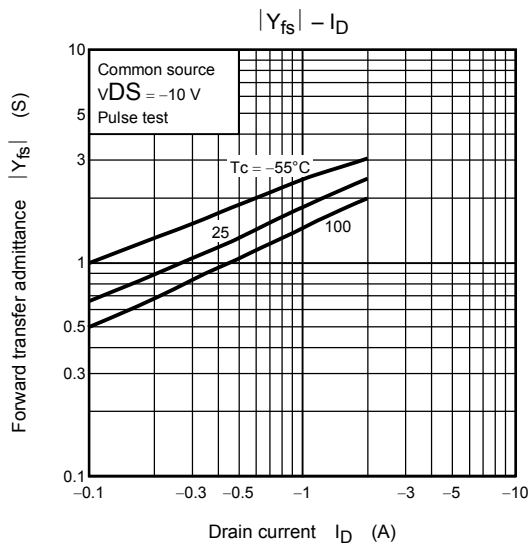
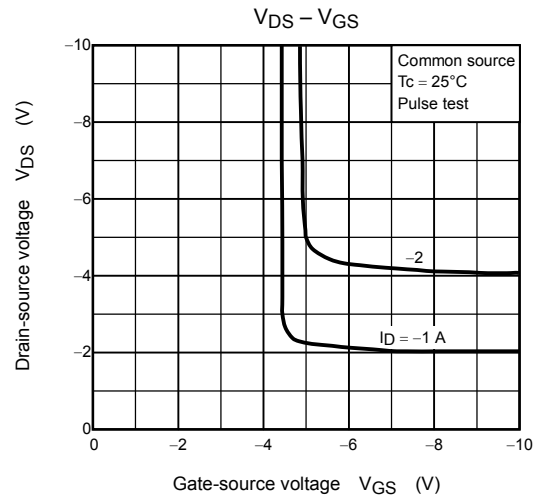
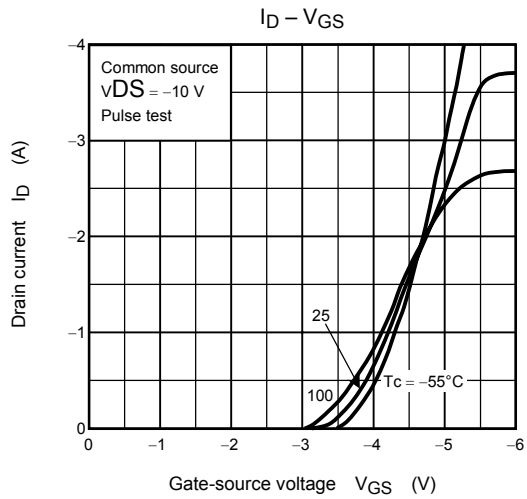
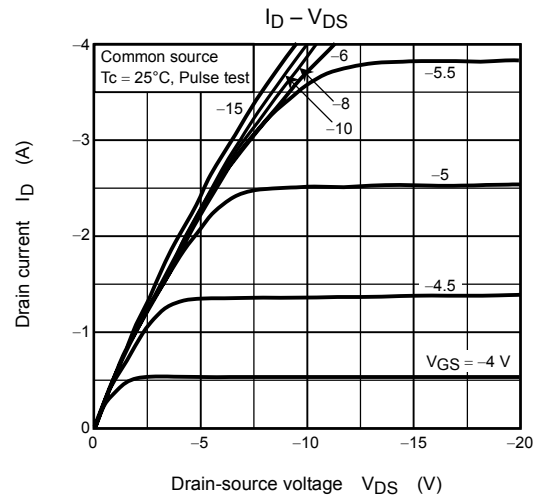
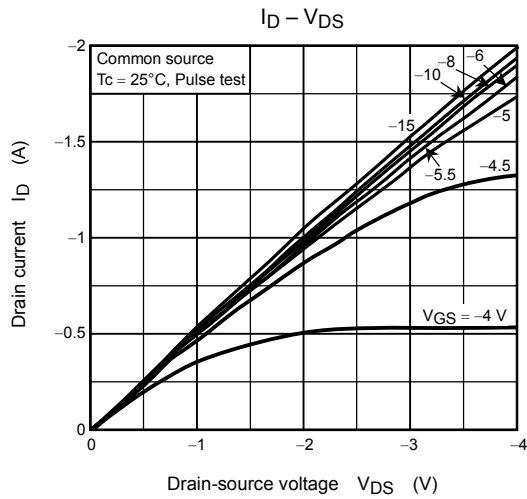
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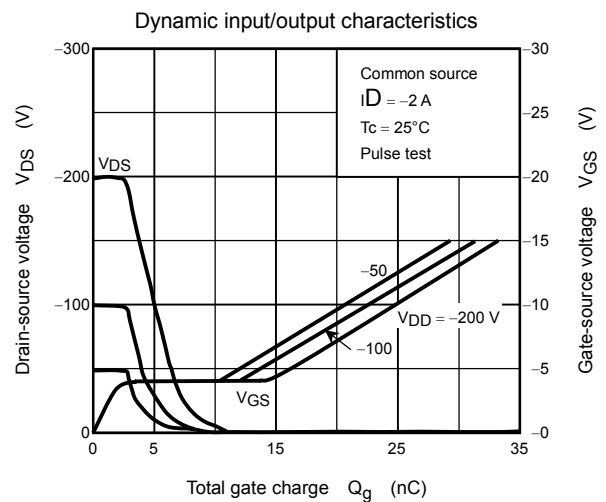
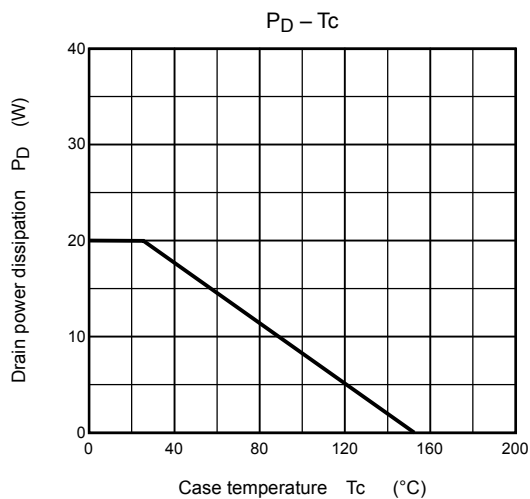
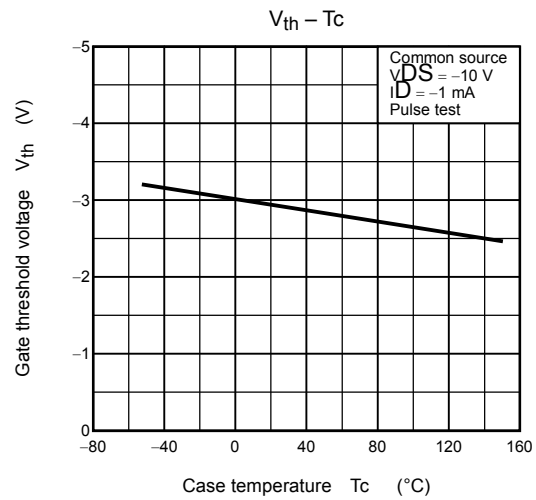
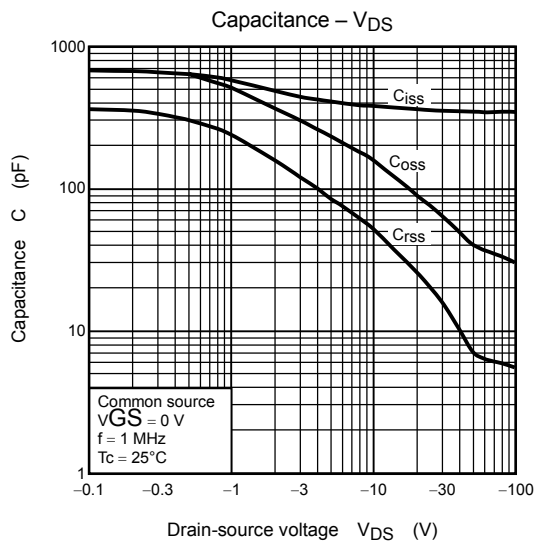
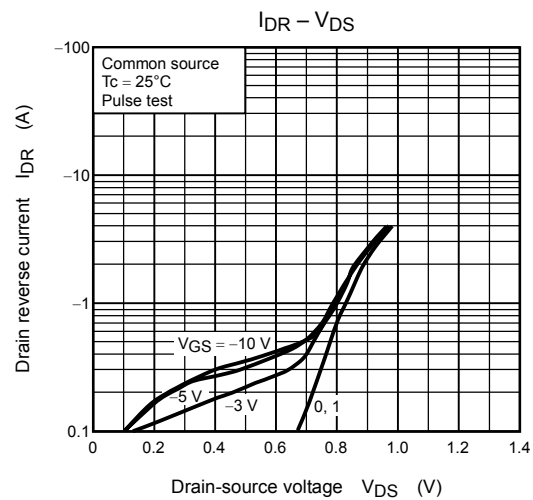
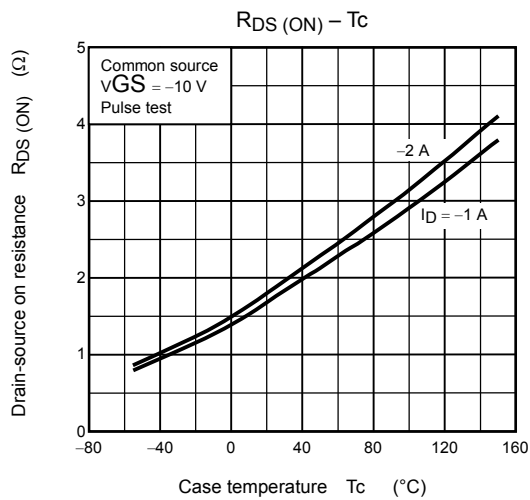


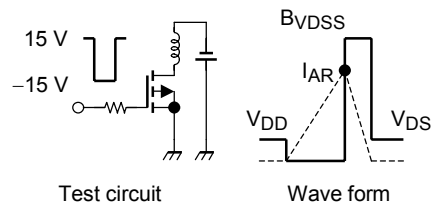
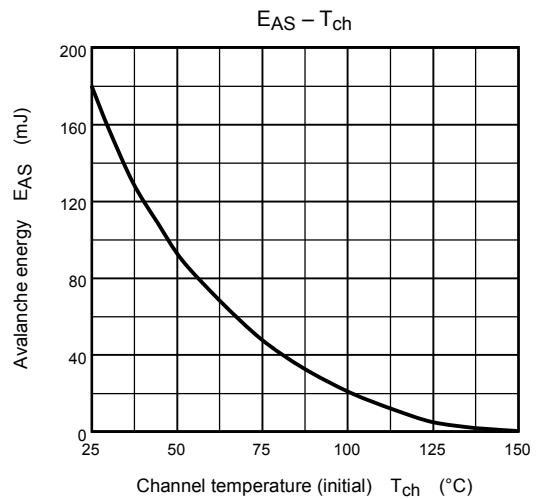
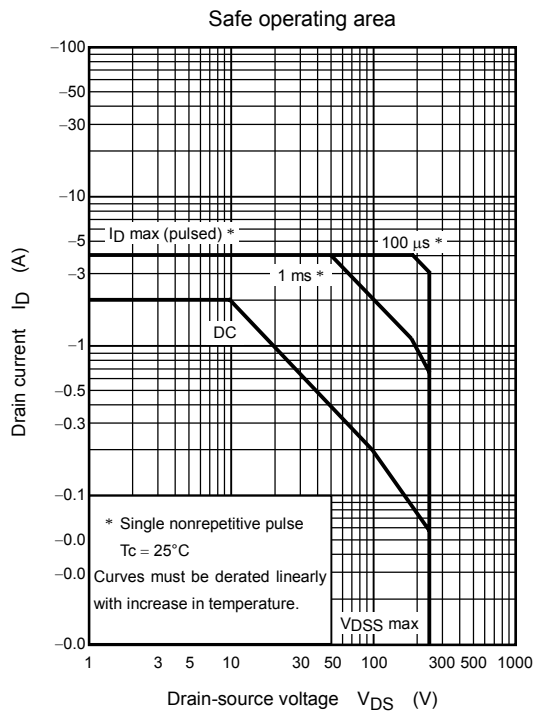
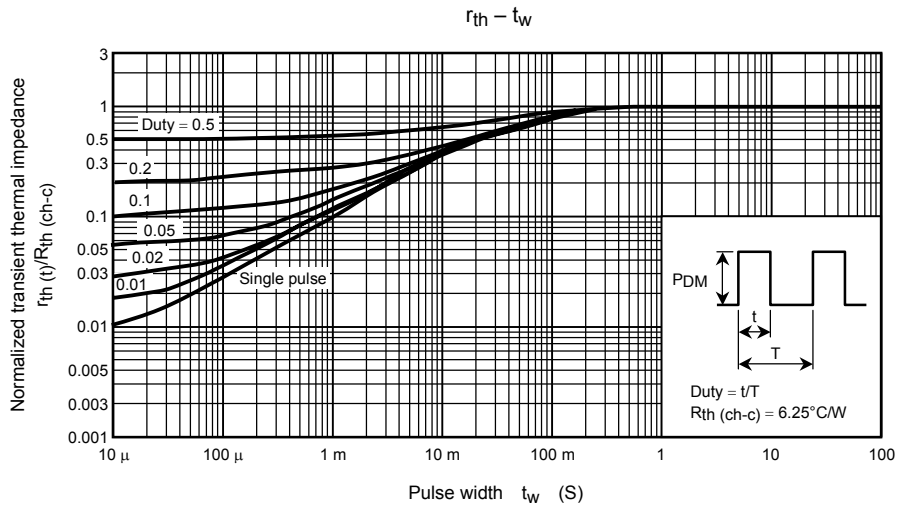
※ Lot Number

Month (starting from alphabet A)

Year (last number of the christian era)







$R_G = 25 \Omega$
 $V_{DD} = -50 \text{ V}$, $L = 75 \text{ mH}$

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